

Title (en)

METHOD FOR THE PREPARATION OF VERMICULAR GRAPHITE CAST IRON AND DEVICE ALLOWING TO IMPLEMENT SUCH METHOD.

Title (de)

VERFAHREN ZUR HERSTELLUNG EINES GUSSEISENS MIT VERMICULARGRAPHIT UND VORRICHTUNG ZUR DURCHFÜHRUNG DES VERFAHRENS.

Title (fr)

PROCEDE DE PREPARATION DE FONTES A GRAPHITE VERMICULAIRE ET DISPOSITIF PERMETTANT D'EXECUTER LE PROCEDE.

Publication

**EP 0074979 A1 19830330 (DE)**

Application

**EP 82900930 A 19820330**

Priority

CH 215881 A 19810331

Abstract (en)

[origin: WO8203410A1] In order to prepare vermicular graphite cast iron in a converter, it is proposed to operate a desulphurization of the primary melting by treating with pure magnesium and alloying to the magnesium, the proportion of Mg to S being in the range from 0.8 to 2.5. The use of titanium of which the bad side effects are known may be avoided. If need be, it is quite possible to pass from the preparation of spheroidal graphite cast iron to the preparation of vermicular graphite cast iron and vice-versa; as a fact, a modification of the starting analysis is not necessary, except for a lower residual magnesium ratio; consequently, a separation of the material in process is not necessary.

Abstract (fr)

En vue de preparer des fontes a graphite vermiculaire dans un convertisseur, il est propose d'operer une desulfuration de la fusion primaire au moyen d'un traitement au magnésium pur et d'allier au magnésium, la proportion de Mg au S étant dans le domaine de 0, 8 a 2, 5. L'on peut alors eviter l'utilisation de titane dont les effets secondaires nefastes sont connus. En cas de besoin, il est sans autre possible de passer de la preparation de fontes a graphite spheroidal a la preparation de fontes a graphite vermiculaire et vice-versa; en effet, une modification de l'analyse de depart n'est pas necessaire; a part le fait d'un taux en magnésium residuaire inferieur; en consequence une separation du materiel en circuit n'est pas necessaire.

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IPC 8 full level

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